

ABSTRACT

In the present invention, conductive dummy patterns continuous in a direction perpendicular to adjacent wiring patterns are inserted at a first distance from the adjacent wiring patterns between the adjacent wiring patterns extending in one direction, in an interconnection wiring layer in an LSI. The insertion of such dummy patterns makes it possible to suppress variations in the degree of pattern density in the interconnection wiring layer and suppress variations in the pattern width in the etching process. Furthermore, since the conductive dummy patterns are continuous in the direction perpendicular to the adjacent wiring patterns, the values of capacitance between the adjacent wiring patterns in the same wiring layer assume a constant value corresponding to the first distance, regardless of the distance between the adjacent wiring patterns.

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